

ESEE 408D
Spring 2003
Homework 4
Due March 6, 2003

Read Chp. 4 and 5 in Baker, Li and Boyce.
Do the following problems from (BLB).

1. In your own words explain why we use highly doped semiconductor regions for the metal-semiconductor contacts and source/drain regions.
2. 4.1
3. 4.6
4. 4.8
5. 4.9
6. 4.10
7. 5.1
8. 5.6